OPA9448H(S)

Infrared LED Chip

GaAlAs/GaAs

1. Material

Substrate GaAs (N Type)
Epitaxial Layer GaAlAs (P/N Type)

2. Electrode

N(Cathode) Side Gold Alloy
P(Anode) Side Gold Alloy

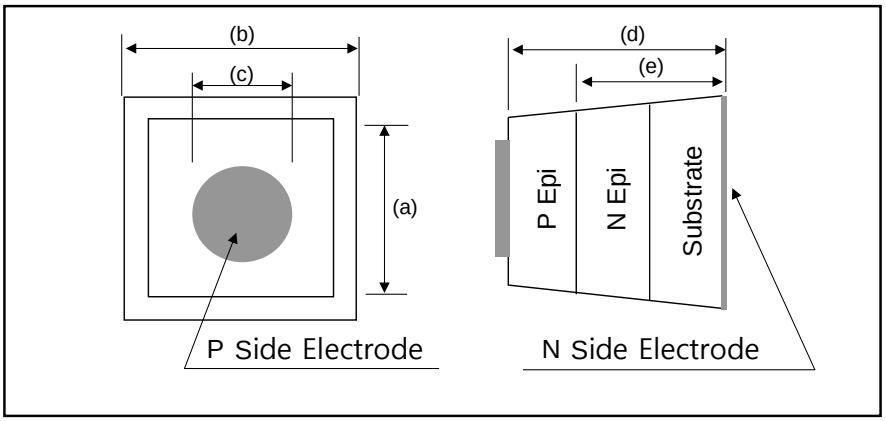
3. Electro-Optical Characteristics

Parameter	Symbol	Min	Typ	Max	Unit	Condition
Forward Voltage	V_F			1.6	V	IF=100mA
Reverse Voltage	V_R	8			V	IR=10uA
Power	P_O	28			mW	IF=100mA
Wavelength	λ_P		940		nm	IF=100mA
	$\Delta\lambda$		55		nm	IF=100mA

※ Note : Power is measured by sorter E/T system with bare chip.

4. Mechanical Data

(a) Emission Area ---------- 11.0mil x 11.0mil
(b) Bottom Area ---------- 12.0mil x 12.0mil
(c) Bonding Pad ---------- 130um
(d) Chip Thickness ---------- 11mil
(e) Junction Height ---------- 6.7mil



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